GANKIBAN: CN10MM

GaN Wafers

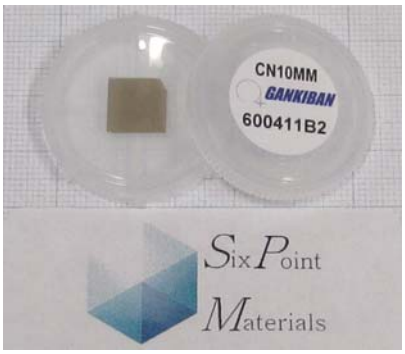
GaN wafers enable "GaN-on-GaN" structure of GaN-based optoelectronic and electronic devices such as blue/green laser diodes, light emitting diodes, high-power switching transistors, and RF transistors. GANKIBAN CN10MM is an n-type wafer produced by SixPoint's proprietary NEAT (near equilibrium ammonothermal) method. It is suitable for vertical devices including edge-emitting laser diodes, vertical high-power pn diodes and vertical high-power transistors.

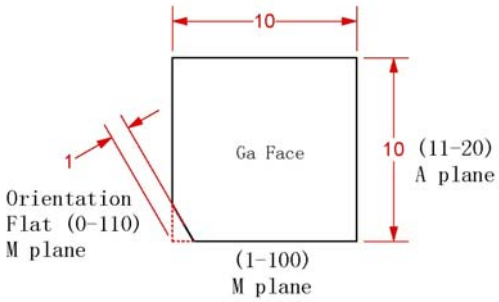
Applications

R&D of GaN-based devices using homoepitaxy

Specifications

Wafer size	10 x 10 mm, with m-plane flat, usable area > 90%
Wafer thickness	300 ~ 400 micron
Orientation	C plane Miscut angle 0°+/-0.15° toward A, 0.4°+/-0.15° toward M
Surface finish	Ga-face --- CMP N-face --- as processed
XRD FWHM from (002)	A grade < 100 arcsec, B grade < 200 arcsec
Conduction type	n-type (n > $1x10^{18}$ cm^{-3})





SixPoint Materials

Contact: Tadao Hashimoto
tadao@spmaterials.com

SixPoint Materials, Inc.
37 Industrial Way, Unit 106,
Buellton, CA 93427
Phone: 805-686-3900, Fax 805-686-3901